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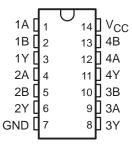
- **EPIC™** (Enhanced-Performance Implanted **CMOS) Process**
- Operating Range 2-V to 5.5-V V_{CC}
- Latch-Up Performance Exceeds 250 mA Per **JESD 17**
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- **Package Options Include Plastic** Small-Outline (D), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) **DIPs**

description

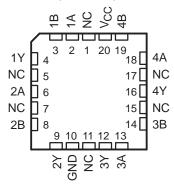
The 'AHC00 devices perform the Boolean function $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive

The SN54AHC00 is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74AHC00 is characterized for operation from -40°C to 85°C.

SN54AHC00 . . . J OR W PACKAGE SN74AHC00 . . . D, DB, DGV, N, OR PW PACKAGE (TOP VIEW)



SN54AHC00 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

FUNCTION TABLE (each gate)

Î	INP	UTS	OUTPUT
ľ	Α	В	Y
ľ	Н	Н	L
I	L	Χ	Н
١	Χ	L	Н



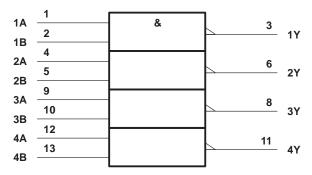
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logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, DGV, J, N, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}		–0.5 V to 7 V
Output voltage range, VO (see Note 1)		–0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)		
Output clamp current, IOK (VO < 0 or VO > VCO	c)	±20 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})		±25 mA
Continuous current through V _{CC} or GND		±50 mA
Package thermal impedance, θ _{JA} (see Note 2):	: D package	86°C/W
•	DB package	96°C/W
	DGV package	
	N package	
	PW package	
Storage temperature range, T _{stg}		

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.



recommended operating conditions (see Note 3)

			SN54A	HC00	SN74A	HC00	UNIT	
			MIN	MAX	MIN	MAX	UNIT	
Vcc	Supply voltage		2	5.5	2	5.5	V	
		V _{CC} = 2 V	1.5		1.5			
VIH	High-level input voltage	$V_{CC} = 3 V$	2.1		2.1		V	
		$V_{CC} = 5.5 \text{ V}$	3.85		3.85			
		V _{CC} = 2 V		0.5		0.5		
VIL	Low-level input voltage	V _{CC} = 3 V		0.9		0.9	V	
		V _{CC} = 5.5 V		1.65		1.65		
٧ı	Input voltage		0	5.5	0	5.5	V	
Vo	Output voltage		0	VCC	0	VCC	V	
		V _{CC} = 2 V		-50		-50	μΑ	
IOH	High-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		-4		-4	mA	
		$V_{CC} = 5 V \pm 0.5 V$		-8		-8	IIIA	
		V _{CC} = 2 V		50		50	μΑ	
lOL	Low-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		4		4	mA	
		$V_{CC} = 5 V \pm 0.5 V$		8		8	IIIA	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 V \pm 0.3 V$		100		100		
ΔυΔν	Input transition rise or fall rate $VCC = 5 V \pm 0.5 V$			20		20	ns/V	
T _A	Operating free-air temperature		-55	125	-40	85	°C	

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T _A = 25°C			SN54AHC00		SN74AHC00		
PARAMETER	TEST CONDITIONS	VCC	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
			1.9	2		1.9		1.9		
	I _{OH} = -50 μA	3 V	2.9	3		2.9		2.9		
Voн		4.5 V	4.4	4.5		4.4		4.4		V
	I _{OH} = -4 mA	3 V	2.58			2.48		2.48		
	I _{OH} = -8 mA	4.5 V	3.94			3.8		3.8		
		2 V			0.1		0.1		0.1	
	I _{OL} = 50 μA	3 V			0.1		0.1		0.1	
VoL		4.5 V			0.1		0.1		0.1	V
	I _{OL} = 4 mA	3 V			0.36		0.5		0.44	
	I _{OL} = 8 mA	4.5 V			0.36		0.5		0.44	
lį	$V_I = V_{CC}$ or GND	0 V to 5.5 V			±0.1		±1*		±1	μΑ
ICC	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20		20	μΑ
C _i	V _I = V _{CC} or GND	5 V		2	10		·		10	рF

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested at $V_{CC} = 0 \text{ V}$.

SN54AHC00, SN74AHC00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

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switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V \pm 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	FROM TO		T _A = 25°C			SN54AHC00		SN74AHC00		UNIT
FARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
t _{PLH}	A or B		C _I = 15 pF		5.5*	7.9*	1*	9.5*	1	9.5	ns
t _{PHL}	AUB	· ·	CL = 15 pr		5.5*	7.9*	1*	9.5*	1	9.5	115
t _{PLH}	A or B		C: - 50 pE		8	11.4	1	13	1	13	nc
t _{PHL}		AOIB	'	C _L = 50 pF		8	11.4	1	13	1	13

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	LOAD	T,	ղ = 25°C	;	SN54A	HC00	SN74A	HC00	UNIT	
FARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT	
^t PLH	A or B	V	C _I = 15 pF		3.7*	5.5*	1*	6.5*	1	6.5	no	
t _{PHL}	AUB	'	CL = 15 pr		3.7*	5.5*	1*	6.5*	1	6.5	ns	
t _{PLH}	A or B	A == D	V	C 50 pF		5.2	7.5	1	8.5	1	8.5	20
t _{PHL}		Ť	C _L = 50 pF		5.2	7.5	1	8.5	1	8.5	ns	

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested.

noise characteristics, $V_{CC} = 5 \text{ V}$, $C_L = 50 \text{ pF}$, $T_A = 25^{\circ}\text{C}$ (see Note 4)

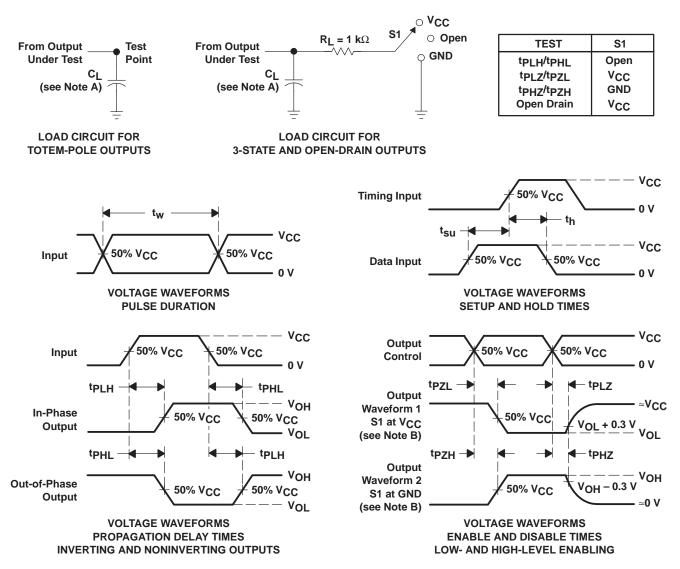
	PARAMETER	SN74AHC00			UNIT
	PARAMETER	MIN TYP MAX 0.3 0.8 -0.3 -0.8 4.6		UNIT	
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}		0.3	0.8	V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.3	-0.8	V
V _{OH(V)}	Quiet output, minimum dynamic VOH		4.6		V
V _{IH(D)}	High-level dynamic input voltage	3.5			V
V _{IL(D)}	Low-level dynamic input voltage			1.5	V

NOTE 4: Characteristics are for surface-mount packages only.

operating characteristics, $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd} Power dissipation capacitance	No load, f = 1 MHz	9.5	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_f \leq 3$ ns, $t_f \leq 3$ ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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